

ABSTRACT OF THE INVENTION

Methods of forming an amorphous etch stop layer by implanting a substrate with an element that is electrically neutral within the substrate are described. The use of elements that are electrically neutral within the substrate prevents electrical interference by the elements if they diffuse to other areas within the substrate. The amorphous etch stop layer may be used as a hard mask in the fabrication of transistors or other devices such as a cantilever.